Tunable Electronic Structure in Gallium Chalcogenide van der Waals Compounds

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Transition metal monochalcogenides comprise a class of two-dimensional materials with electronic band gaps that are highly sensitive to material thickness and chemical composition. Here, we explore the tunability of the electronic excitation spectrum in GaSe using angle-resolved photoemission spectroscopy. The electronic structure of the material is modified by in-situ potassium deposition as well as by forming GaSxSe1−x alloy compounds. We find that potassium decouples the topmost tetra-layer of the GaSe unit cell, leading to a substantial change of the dispersion around the valence band maximum (VBM). The observed band dispersion of a single tetralayer is consistent with a transition from the direct gap character of the bulk to the indirect gap character expected for monolayer GaSe. Upon alloying with sulfur, we observe a phase transition from AB to AA stacking. Alloying also results in a rigid energy shift of the VBM towards higher binding energies which correlates with a blue shift in the luminescence. The increase of the band gap upon sulfur alloying does not appear to change the dispersion or character of the VBM appreciably, implying that it is possible to engineer the gap of these materials while maintaining their salient electronic properties.

I. INTRODUCTION

The ability to isolate monolayers and study their physical properties has led to a resurgence of interest in layered van der Waals (VDW) materials as two-dimensional systems. Transition-metal chalcogenides belong to this class of materials and demonstrate unique thermoelectric, photonic and electronic properties. The composition, phase, and crystal structure of these materials can be tuned to display a wide range of electronic phases including metallic, semiconducting, superconducting and charge-density wave phases, inspiring utilization in a wide range of applications including electronic devices, sensors, and quantum devices.

In their bulk form, monochalcogenides of Ga and In, such as GaSe, InSe, and GaS are van der Waals compounds. Gallium chalcogenides (GCs) are direct bandgap semiconductors that can be mechanically exfoliated from a bulk parent crystal. Their properties are highly sensitive to material thickness, chemical composition, and crystalline structure. Bulk GaSe and GaS have direct band gaps of 2.10 eV and 3.05 eV, respectively, and transition to indirect gaps when the number of layers is reduced. Monolayer field effect devices maintain mobilities on the order of 0.1 cm2V−1 s−1, on/off ratios of 104 - 105 as well as quantum efficiencies that exceed those of graphene by several orders of magnitude when implemented in a device architecture.

Alloys with mixed chalcogen content, GaSxSe1−x, allow for control of the bandgap, allowing engineering of the optical absorption and photoluminescence (PL) interlayer coupling, defects, doping, and interaction with an underlying substrate may further modify the electronic structure of the GCs, as observed in exfoliated flakes of GaSe and GaTe on SiO2 and graphite, and epitaxially grown GaSe flakes on graphene.

In this communication, we illustrate how the crystalline and electronic properties of GC materials are affected by changes in chemical composition, doping, and reduced dimensionality using high resolution scanning transmission electron microscopy (HRSTEM), angle-resolved photoemission spectroscopy (ARPES), and PL.

HRSTEM reveals that GaSe tetralayers stack in the AB sequence (α phase) while sulfur alloys and GaS stack almost exclusively in the AA’ sequence (β phase). The complete E(kx,ky,kz) electronic structure of AB-stacked GaSe is determined using ARPES, allowing us to directly extract the band dispersion along high symmetry directions and determine valence band (VB) extrema and effective masses. We illustrate how the full energy-momentum-resolved quasiparticle band structure of the GCs is modulated when the chemical composition and/or interaction between layers is changed. We explore the influence of potassium deposition on the band structure, finding it only causes a slight doping-induced shift of the VBs and does not lead to degenerate doping which would enable ARPES visualization of the conduction band. However, potassium dosing does lead to a decoupling of surface GaSe layers from the bulk, allowing us to measure the band structure in the 2D limit. Finally, we explore the effect of sulfur alloying on the band structure. We find that increasing sulfur content produces a
rigid VB shift and results in a corresponding blue shift in the PL, suggesting that alloying is a viable method for tuning GC optical properties.

II. EXPERIMENTAL

We study pure GaSe and GaS as well as three alloy compositions spanning the entire compositional range of GaS$_x$Se$_{1-x}$ alloys. Crystals are grown using the modified Bridgman-Stockbarger method. Briefly, stoichiometric amounts of Ga, S, and Se powder are weighed and mixed in sealed quartz ampoules to achieve the desired alloying ratio. The Ampoules are then heated in a zone furnace at 970 °C for two weeks to grow single crystals 2-8 mm in diameter.

The HRSTEM samples are prepared by a two-step process. First, the crystals are cleaved using blue wafer dicing tape and transferred to Si substrates coated with 100 nm thick SiO$_2$. Next, a Cu TEM grid with carbon film is adhered to flakes on the Si/SiO$_2$ wafer using a drop of isopropanol. Once the drop has dried, the SiO$_2$ is etched away using 1M NaOH. Lastly the grid is washed in deionized water and dried prior to imaging. HRSTEM is carried out using a double $C_s$ corrected FEI Titan 80-300 operating at an accelerating voltage of 80 kV at the Molecular Foundry.

For ARPES measurements, large crystals of GCs are glued to a Cu sample holder using epoxy and cleaved in-situ in the ultra-high vacuum (UHV) chamber with a base pressure better than 5×10$^{-11}$ mbar. The samples are cooled to 85 K prior to cleaving and kept at this temperature during ARPES measurements. The cleaved single-crystal domain sizes are on the order of 100 µm as defined by spatially scanning the sample with the synchrotron beam. The ARPES data are collected at the Microscopic and Electronic Structure Observatory (MAESTRO) at the Advanced Light Source (ALS) using the microARPES end-station equipped with a hemispherical Scienta R4000 analyzer. The beamline slit settings are adjusted so that the size of the beam is on the order of 20 µm. VB and Ga 3d core level spectra are obtained primarily using a photon energy of 94 eV. S 2p and Se 3p core level data are collected using a photon energy of 300 eV. Photon energy scans of GaSe are acquired for photon energies between 21 eV and 140 eV. In order to relate the photoelectron kinetic energy, $E_{\text{kin}}$, to the out-of-plane momentum, $k_z$, we use the free-electron final state assumption where $k_z^2 = (2m/\bar{h}^2)(E_{\text{kin}} + V_0)$, where $V_0$ is the inner potential. We find that $V_0 = 10.2$ eV provides the best description of the data, given the out-of-plane lattice constant $c = 15.96$ Å and the Brillouin zone (BZ) periodicity of $2\pi/c$ for the measured polytypes of GaSe. Potassium dosing experiments on GaSe are carried out in-situ using SAES getters mounted in the analysis chamber. The total energy and momentum resolution in the ARPES data are better than 20 meV and 0.01 Å$^{-1}$, respectively.
III. RESULTS AND DISCUSSION

A. HRSTEM Measurements of Gallium Chalcogenides

The GaS$_x$Se$_{1-x}$ system forms a continuous set of alloys for the entire compositional range $0 \leq x \leq 1$ of the stoichiometry$^{30,32}$. Like other layered VdW materials, the intralayer bonding is strong and mostly covalent while the interlayer bonding is weak and of VdW character. The unit cell consists of two tetrahedral pyramids stacked tip to tip with chalcogen atoms at the base and a Ga atom at the apex, forming a four-atom-thick tetralayer.

The layer stacking exhibits several different polytypes, depending on composition and growth conditions. In the $\varepsilon$ phase (Fig. 1(a-b)), successive tetralayers are stacked in the sequence AB, resulting in Ga atoms from the A layer being vertically aligned with chalcogen atoms in the B layer, and chalcogen atoms in the A layer being vertically aligned with the interstitial voids in the centers of the hexagons from the B layer, similar to Bernal stacking in graphite. The inversion symmetric $\beta$ phase (Fig. 1(e-f)) is obtained by stacking successive tetralayers in the sequence AA’, resulting in Ga(chalcogen) atoms from the A layer eclipsing chalcogen(Ga) atoms from the A’ layer. The system can also form the rhombohedral $\gamma$ phase (ABC stacking), but this stacking sequence is not observed experimentally in our samples.

Previous studies have explored the relationship between sulfur content and stacking phase$^{30,32}$. GaS$_x$Se$_{1-x}$ alloys with low sulfur content ($x < 0.15$) stack in the $\varepsilon$ phase while alloys with higher sulfur content ($x > 0.35$) display the $\beta$ stacking phase. Our experimental results (described below) also show this trend. We find that the $\varepsilon$ phase occurs for $x \leq 0.3$ and the $\beta$ phase for $x > 0.3$. The $\beta$ and $\varepsilon$ phases are thought to co-exist for intermediate sulfur content ($0.15 < x < 0.35$), phase segregated throughout the crystal, but our samples do not show experimental evidence for this theory.

Contrast in HRSTEM indicates differences in atomic number, density, and thickness throughout a specimen. Due to the specific stacking sequences exhibited by the polytypes of GaS$_x$Se$_{1-x}$ alloys and the contrast mecha-
nisms of STEM imaging, our imaging experiments (Fig. 1(c) and 1(g)) unambiguously reveal the stacking phases of these materials.

Figure 1(c) shows a typical HRSTEM image for an alloy with high sulfur content (x ~ 0.75), appearing as a trigonal lattice with alternating bright and dim atomic columns. Figure 1(d) shows a line plot of the intensity extracted from the region outlined by the red rectangle in Fig. 1(c). The heights of the peaks in the line trace indicate that there are approximately twice as many atoms in bright columns compared to the dim columns, consistent with the stacking geometry of the ε phase, shown in Fig. 1(b). Figure 1(g) shows an analogous image for pure GaSe which appears as a honeycomb mesh of atomic columns with no appreciable intensity in the interstitial voids between hexagons. The line profile (Fig. 1(h)) shows that the atomic columns have uniform intensity, consistent with AA′ stacking exhibited by the β phase.

B. ARPES Electronic Structure Measurements of GaSe

An overview of the electronic band structure of pristine GaSe is presented in Fig. 2. The data are acquired at a photon energy of 94 eV, which probes the Γ−K−M plane as described by the BZ sketches in Fig. 2(a). Figures 2(b)-(c) show cuts along the Γ−K−M and Γ−M−Γ high symmetry directions as signified by the dashed lines in Fig. 2(a). The evolution of the dispersion with binding energy is presented via the constant binding energy cuts in Fig. 2(d)-(h), which reveal the trigonal symmetry of the dispersion as well as strong intensity variations between the bands in the BZs. The valence band maximum (VBM) is situated at Γ and is characterized by a parabolic-shaped lobe. The location of the VBM at Γ is consistent with theoretical predictions that GaSe is a direct-gap semiconductor with the conduction band minimum (CBM) also located at Γ point. Additional sub bands dispersing towards M and K appear above binding energies of 1.5 eV. The material remains rather featureless away from Γ before the onset of this higher binding energy range, implying most of the optical properties of GaSe will derive from the central parabolic lobe. The ARPES data discussed here are fully consistent with the electronic structure data presented in Ref. [33].

We investigate the k_z-dispersion in the three dimensional BZ of GaSe shown in Fig. 3(a). By measuring the photon energy dependence of the dispersion at normal emission we are able to trace the band structure along the Γ−A direction, as seen in Fig. 3(b). A strong k_z-dispersion is visible in the center of the parabolic lobe, which is further highlighted via the fits (open circles) and guide line in Fig. 3(b), whereas the bands at binding energies higher than 1.5 eV have a much more flat k_z-dispersion. The fitted dispersion reveals an apparent BZ doubling effect; however, this occurs due to a suppression of the photoemission intensity in adjacent BZs, similar to observations in photoemission experiments on graphite [35,36]. The band structure along the Γ−K line is shown for two neighboring BZs in the k_z direction in Fig. 3(c-d). The main intensity moves from the bottom corner of the parabolic lobe in Fig. 3(c) to the VBM in Fig. 3(d). Similar intensity variations are observed in neighboring in-plane BZs, as sketched in Fig. 3(e). The (k||, k_z)-contour at a binding energy of 0.2 eV shown in Fig. 3(f) shows a cut around the VBM for the Γ−A−L−M plane (see Fig. 3(e)). The intensity maxima are seen to shift between the 1st and 2nd BZs and the absolute intensity levels also vary strongly within the same BZ. A cut along the Γ−M line at k_z = 4.75 Å⁻¹ in Fig. 3(g) shows the upper VB parabolic lobe in two neighboring zones. In the first BZ, the intensity is concentrated in the bottom corner while in the 2nd BZ the intensity is concentrated around the VBM.

This behavior can be reconciled with the orbital character of the bands, previously studied with detailed...
The effect of K dosing of bulk GaSe is explored in Fig. 4. Alkali metal deposition offers a possibility to chemically dope the material. The ARPES measurements along the \( \Gamma - K - M \) direction in Fig. 4(a-b) before and (b) after K dosing. The observed strong change of band structure points towards a change of the interlayer electronic interactions in the K-dosed GaSe. The band structure in the K doped case strongly resembles the expected single-layer GaSe band structure predicted by theory, where the material has undergone a transition to an indirect gap semiconductor. This single-layer character of the band structure is also evident in the cut of the bulk band structure shown in Fig. 3(c).

In the K-doped case, the band gap transition is most likely induced by the deposited K atoms, as they may electronically decouple the GaSe tetralayers by disrupting the interlayer coupling of the Se \( p_z \) orbitals. The decoupling can be facilitated by K intercalation in the van der Waals gap between the layers, as observed in metallic and semiconducting transition metal dichalcogenides, or by a chemical interaction on the surface of the crystal, which significantly changes the coupling between individual layers as seen in graphene multilayers.

In order to probe the interaction between GaSe and K, we monitor the Ga 3d core level during the dosing experiment. Figure 4(f)-(g) present the clean and fully K dosed cases. A new component, which we attribute to an interaction between Ga and K, is extracted via line shape analysis, as seen in Fig. 4(g). These new core-level components are fully consistent with the observed band structure changes.

FIG. 4. (color online) Effect of K dosing on the GaSe electronic structure. (a)-(b) ARPES Measurements of the dispersion in the \( \Gamma - K - M \) direction (a) before and (b) after K dosing. The dashed curves present the fitted location of the VBM peak intensity. (c) Location of the VBM peak intensity (open circles) fitted with a 2nd order and a 4th order polynomial for the clean and K doped samples, respectively. (d) EDCs (open circles) and results of Voigt function fits (curves) in the clean and K doped cases. The EDCs were extracted at \( \Gamma \) along the lines shown in (a)-(b). The position of the top-most peak is plotted via dashed lines in (a)-(b) and open circles in (c). (e) Evolution of the photoemission intensity at \( \Gamma \) as a function of K dosing steps. The open circles and guidelines mark the fitted peak positions obtained by performing the EDC analysis shown in (d) in each K dosing step. (f)-(g) Ga 3d core level measurements (f) before and (g) after K dosing. The data (thick red curves) have been fitted (dashed curves) with Doniach-Sunjic line shapes (filled peaks) for each of the observed components.

C. Potassium Deposition of GaSe

Since the states near the VBM are mainly of Se \( p_z \) character, the interlayer interactions will cause intensity modifications reflecting the coupling of the GaSe tetralayers, leading to a dispersion resembling a single tetralayer for the \( k_z \) value used for the slice shown in Fig. 3(c), while the \( k_z \) value for Fig. 3(d) shows a dispersion with a more bulk-like character. The subbands just below the VBM exhibit less dramatic behavior due to the \( p_x(y) \) character of these states which are less sensitive to the adjacent GaSe tetralayers.

The EDCs extracted at normal emission in Fig. 4(d) trace the peak positions at each K dosing step. Voigt line shapes have been fitted to each of the peaks, which have been plotted together with the photoemission intensity at normal emission at each K dose in Fig. 4(e). The observed strong change of band structure points towards a change of the interlayer electronic interactions in the K-dosed GaSe. The band structure in the K doped case strongly resembles the expected single-layer GaSe band structure predicted by theory, where the material has undergone a transition to an indirect gap semiconductor. This single-layer character of the band structure is also evident in the cut of the bulk band structure shown in Fig. 3(c).
D. ARPES and PL Measurements of GaS\textsubscript{x}Se\textsubscript{1−x} alloys

GaS\textsubscript{x}Se\textsubscript{1−x} alloys offer a promising route to tune the optical gap and luminescent properties of III-VI semiconductors. However, it is unknown how robust the electronic structure remains between different alloys. Here we compare pristine GaSe with two different GaS\textsubscript{x}Se\textsubscript{1−x} alloys (alloys I and II). The stoichiometry \( x \) is checked via core level measurements of the Se 3p and S 2p binding energy regions, shown in Fig. 5. By comparing the spectral weight of the Se 3p core levels, we are able to estimate that the composition of alloy I is \( x = 0.27 \pm 0.05 \) and the composition of alloy II is \( x = 0.61 \pm 0.05 \). These values are consistent when we perform the same analysis on the Se 3d core levels (not shown). The core level data is consistent with the stoichiometry of precursor added to the growth ampoule.

Figure 6(a)-(c) present ARPES measurements of the VBs for the three systems. The overall band dispersion is found to be very similar with a constant effective mass of
\[
m^* = (1.1 \pm 0.2)m_0.
\]

The binding energy position of the VBM changes significantly between the three systems, consistent with a change of the electronic band gap. It is also possible that Fermi level pinning plays a strong role for the band positions, as the defect concentration is likely different in the alloys. PL measurements, shown in Fig. 6(d), reveal a change of the optical gap. The PL peak positions plotted in Fig. 6(e) indicate that the optical gap increases as more S is added in the alloy. The same trend is seen for the VBM binding energy position in Fig. 6(f), which fits with a simultaneous increase of the quasiparticle band gap. The trend determined here is fully consistent with optical absorption measurements of GaS\textsubscript{x}Se\textsubscript{1−x}.\textsuperscript{22} Note that ARPES measurements of pure GaS were attempted but the sample was found to charge too severely, which is likely due to the larger band gap of the material compared to the other GaS\textsubscript{x}Se\textsubscript{1−x} compounds investigated here.

The \( \varepsilon \) and \( \beta \) stacking phases observed in HRSTEM are not expected to give rise to striking differences in the electronic structure.\textsuperscript{27,29} However, detailed inspection of the measurements in Fig. 6(a)-(c) do show some variations in the intensity and structure of the dispersive bands in the higher binding energy region above the central VB lobe. While different stacking phases may affect the photoemission intensity, the change in chemical environment caused by the mixed chalcogen content directly influences the in-plane \( p_{x(y)} \) orbitals that the higher binding energy bands are composed of, thereby leading to the possibility of a modified dispersion.
We have measured the bulk electronic structure of GaSe using ARPES and thereby identified the bulk band dispersion, the structure of the VBM, and the complex photoemission intensity variations associated with the tetralayer unit cell. Potassium deposition of GaSe leads to a dramatic change of the VBM dispersion and binding energy position. Our data are consistent with an increased band gap and a transition from a direct to an indirect band gap semiconductor when the K atoms decouple the top-most GaSe tetralayer. We have investigated the effect of sulfur alloying on the crystalline and electronic structure and used HRSTEM to observe a transition from the $\varepsilon$ phase to the $\beta$ phase for sulfur content above $\sim$30 percent. We have also shown that alloying causes a rigid shift of the VBM binding energy position without a significant change in the actual band dispersion around the VBM. This rigid shift is consistent with an increase in the optical band gap measured by PL.

**IV. CONCLUSION**

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